

IN THE SPECIFICATION

Please amend the paragraph beginning on page 4, line 6, as follows:

Next, using the resist pattern 112 as a mask, the patterns of the polysilicon film 111 and polysilicon film 109 are formed by an etching process. Then, after releasing the resist pattern 112, a step forming an LDD region 113, a step of forming a side wall 114 of a gate electrode, and a step of forming [a] diffusion ~~layer~~ layers 115, 116 are carried out. Further, an N type transistor and a P type transistor are formed through a post-oxidization step at 800°C and for about 600 minutes. Of course, at this heating step as well, the impurity of boron “B” slightly introduced into the silicon substrate 101 diffuses over the wide area of silicon substrate 101.